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## Conductance and gating effects at sputtered oxide interfaces

Yin, C.

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# **Conductance and Gating Effects at Sputtered Oxide Interfaces**

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**Chunhai Yin**

geboren te Cangzhou, China  
in 1987

Promotor:

Prof. dr. J. Aarts

Universiteit Leiden

Promotiecommissie:

Dr. A. D. Caviglia

Technische Universiteit Delft

Prof. dr. J. Santamaria

Universidad Complutense Madrid

Prof. dr. E. R. Eliel

Universiteit Leiden

Prof. dr. ir. T. H. Oosterkamp

Universiteit Leiden

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About the cover: The cover shows an illustration of the  $\text{LaAlO}_3/\text{SrTiO}_3$  interface. The left side is the  $\text{LaAlO}_3$  film and the right side is the  $\text{SrTiO}_3$  substrate. The light blue, dark blue, orange, red and gray spheres represent La, Al, Sr, Ti and O atoms, respectively. The light gray squares represent oxygen octahedra.

*To my grandfather*



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